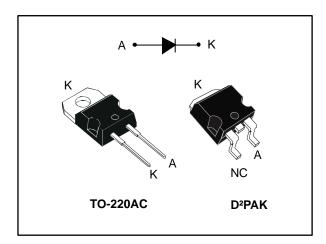


## STPSC10H12-Y

## Automotive grade 1200 V power Schottky silicon carbide diode

Datasheet - production data



### **Features**

- AEC-Q101 qualified
- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- PPAP capable
- Operating T<sub>j</sub> from -40 °C to 175 °C
- ECOPACK®2 compliant

### **Description**

The SiC diode, available in TO-220AC and D²PAK, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low  $V_F$  Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC and secondary side applications, this ST SiC diode will boost the performance in hard switching conditions. This rectifier will enhance the performance of the targeted application. Its high forward surge capability ensures a good robustness during transient phases.

**Table 1: Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	10 A
$V_{RRM}$	1200 V
T <sub>i</sub> (max.)	175 °C
V₅(typ.)	1.35 V

Characteristics STPSC10H12-Y

### 1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Р		Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage	e (T <sub>j</sub> = -40 °C to +175 °C	C)	1200	V
I <sub>F(RMS)</sub>	Forward rms current			25	Α
I <sub>F(AV)</sub>	Average forward current	T <sub>C</sub> = 155 °C, DC curre	nt	10	Α
I <sub>FRM</sub>	Repetitive peak forward current	$T_C = 155 ^{\circ}C, T_j = 175 ^{\circ}$	38	Α	
		4. 40 mag aigus aidal	T <sub>C</sub> = 25 °C	71	
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal	T <sub>C</sub> = 150 °C	60	Α
	Carrone	t <sub>p</sub> = 10 μs square	T <sub>C</sub> = 25 °C	420	
T <sub>stg</sub>	Storage temperature range	-65 to +175	°C		
Tj	Operating junction temperature	-40 to +175	°C		

**Table 3: Thermal parameters** 

Symbol	Parameter	Тур.	Max.	Unit
R <sub>th(j-c)</sub>	Junction to case	0.65	0.9	°C/W

**Table 4: Static electrical characteristics** 

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
1 (1)	Deverage legicone augment	T <sub>j</sub> = 25 °C	\/ \/	-	5	60	
IR''	I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 150 °C	$V_R = V_{RRM}$	-	30	400	μA
V <sub>F</sub> (2)	Commend weltone dree	T <sub>j</sub> = 25 °C	1 40 4	-	1.35	1.50	\/
VF <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 150 °C	I <sub>F</sub> = 10 A	-	1.75	2.25	V

### Notes:

 $^{(1)}$ Pulse test:  $t_p$  = 10 ms,  $\delta$  < 2%

 $^{(2)}$ Pulse test:  $t_p$  = 500  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses use the following equation:

 $P = 1.03 \text{ x } I_{F(AV)} + 0.122 \text{ x } I_{F^2(RMS)}$ 

**Table 5: Dynamic electrical characteristics** 

Syn	nbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Qo	Cj <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 800 V	1	57	ı	nC
	C <sub>i</sub> Total capacitance		$V_R = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ MHz}$	-	725	-	٦
	<b>J</b> j	Total capacitance	V <sub>R</sub> = 800 V, T <sub>c</sub> = 25 °C, F = 1 MHz	-	47	-	pF

#### Notes:

<sup>(1)</sup>Most accurate value for the capacitive charge:  $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$ 



STPSC10H12-Y Characteristics

V<sub>F</sub>(V)

2.5

2.0

### 1.1 Characteristics (curves)

0.5

Figure 1: Forward voltage drop versus forward current (typical values)

Figure 2: Reverse leakage current versus reverse voltage applied (typical values)

I<sub>R</sub>(μA)

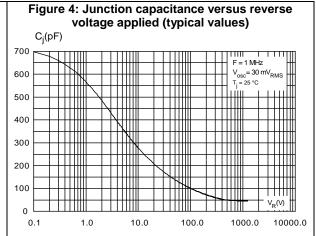
1.E+02

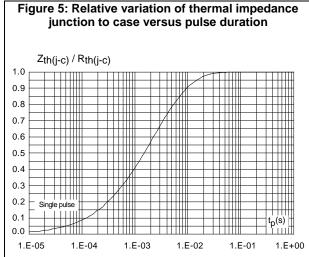
1.E+01

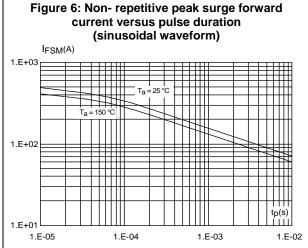
1.E-03

0 100 200 300 400 500 600 700 800 900 10001100 1200

Figure 3: Peak forward current versus case temperature  $I_{M}(A)$ 100 80 60  $\delta = 0.3$ 40 20 δ = 1  $\delta = 0.7$ 0 0 25 50 75 100 125 150 175



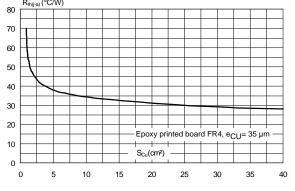




Characteristics STPSC10H12-Y

Figure 7: Total capacitive charges versus reverse voltage applied (typical values) 60 50 40 30 20 10  $V_{R}(V)$ 0 0 100 200 300 400 500 600 700 800

Figure 8: Thermal resistance junction to ambient versus copper surface under tab for D2PAK package (typical values)  $R_{th(j-a)}$  (°C/W)



4/10 DocID029346 Rev 2 STPSC10H12-Y Package information

#### 2 **Package information**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.7 N·m

#### **TO-220AC** rectifier package information 2.1

**H2** Ø١ L5 **L7** L6 L2 D L9 F1 L4 М Ε G

Figure 9: TO-220AC package outline

577

Table 6: TO-220AC package mechanical data

	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
Е	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
H2	10.00	10.40	0.393	0.409	
L2	16.40	O typ.	0.645	ō typ.	
L4	13.00	14.00	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6 typ.		0.102	2 typ.	
Diam	3.75	3.85	0.147	0.151	

STPSC10H12-Y Package information

# 2.2 D<sup>2</sup>PAK package information

Figure 10: D<sup>2</sup>PAK package outline

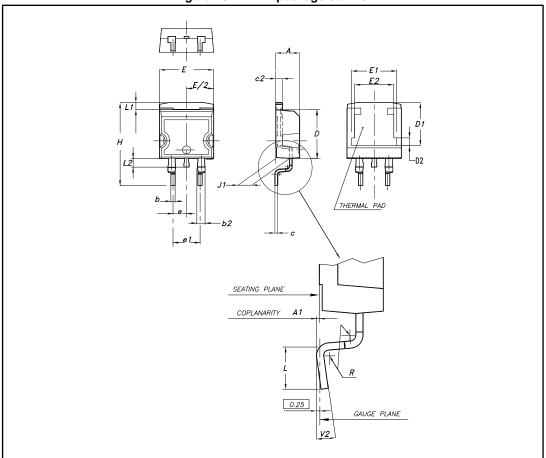
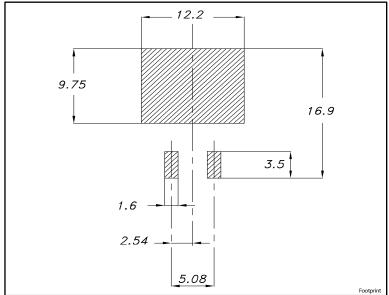


Table 7: D2PAK package mechanical data

	Dimensions						
Ref.		Millimeters	;		Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	4.40		4.60	0.173		0.181	
A1	0.03		0.23	0.001		0.009	
b	0.70		0.93	0.028		0.037	
b2	1.14		1.70	0.045		0.067	
С	0.45		0.60	0.018		0.024	
c2	1.23		1.36	0.048		0.053	
D	8.95		9.35	0.352		0.368	
D1	7.50	7.75	8.00	0.295	0.305	0.315	
D2	1.10	1.30	1.50	0.043	0.051	0.060	
Е	10		10.40	0.394		0.409	
E1	8.50	8.70	8.90	0.335	0.343	0.346	
E2	6.85	7.05	7.25	0.266	0.278	0.282	
е		2.54			0.100		
e1	4.88		5.28	0.190		0.205	
Н	15		15.85	0.591		0.624	
J1	2.49		2.69	0.097		0.106	
L	2.29		2.79	0.090		0.110	
L1	1.27		1.40	0.049		0.055	
L2	1.30		1.75	0.050		0.069	
R		0.4			0.015		
V2	0°		8°	0°		8°	

Figure 11: D<sup>2</sup>PAK recommended footprint (dimensions are in mm)



8/10 DocID029346 Rev 2

STPSC10H12-Y Ordering information

# 3 Ordering information

**Table 8: Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC10H12DY	STPSC10H12DY	TO-220AC	1.86 g	50	Tube
STPSC10H12GY-TR	STPSC10H12GY	D²PAK	1.48 g	1000	Tape and reel

## 4 Revision history

**Table 9: Document revision history** 

Date	Revision	Changes
05-Jan-2017	1	Initial release.
23-Jan-2017	2	Added D <sup>2</sup> PAK package.

### **IMPORTANT NOTICE - PLEASE READ CAREFULLY**

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2017 STMicroelectronics - All rights reserved

